

Description

The IPD088N06N3G uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

TO-252-2L

General Features

 $V_{DS} = 60V I_{D} = 80 A$

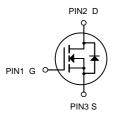
 $R_{DS(ON)}$ < 8.3 m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IPD088N06N3G	TO-252-2L	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units
V _D s	Drain-Source Voltage	60	V
Vgs	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	ent, V _{GS} @ 10V ¹ 80	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	V _{GS} @ 10V ¹ 40	
Ірм	Pulsed Drain Current ²	255	А
las	Avalanche Current	23	А
P _D @T _C =25°C	Total Power Dissipation ⁴	100	W
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
R _θ JA	Thermal Resistance Junction-Ambient ¹	62.5	°C/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	-	-	V
Rds(on)	Static Drain-Source On- Resistance ²	V _{GS} =10V, I _D =45A	-	6	8.3	mΩ
		V _{GS} =6V, I _D =30A	-	13	17	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.4	3	V
g fs	Forward Transconductance	V _{DS} =10V, I _D =30A	-	71	-	S
IDSS	Drain-Source Leakage Current	V _{DS} =60V, V _{GS} =0V	-	-	10	uA
	Drain-Source Leakage Current (T _j =125°C)	V _{DS} =48V ,V _{GS} =0V	-	-	250	uA
Igss	Gate-Source Leakage	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Qg	Total Gate Charge	I _D =30A	-	33	45	nC
Qgs	Gate-Source Charge	V _{DS} =48V V _{GS} =4.5V	-	5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge		-	21	-	nC
td(on)	Turn-on Delay Time	V _{DS} =30V	-	10	-	ns
t _r	Rise Time	I _D =30A		43	-	ns
t _{d(off)}	Turn-off Delay Time	$R_G=3.3\Omega$	-	47	-	ns
t _f	Fall Time	V _{GS} =10V	-	80	-	ns
Ciss	Input Capacitance		-	2680	3300	pF
Coss	Output Capacitance	V _{GS} =0V	-	260	-	pF
Crss	Reverse Transfer Capacitance	V _{DS} =25V f=1.0MHz	-	180	-	pF
V _{SD}	Forward On Voltage ²	I _S =45A, V _{GS} =0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _S =10A, V _{GS} =0V, dI/dt=100A/µs	-	30	_	ns
Qrr	Reverse Recovery Charge		-	18	-	nC



Typical Performance Characteristics

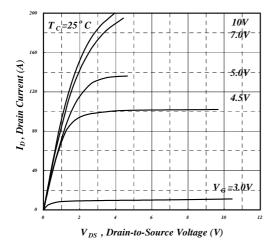


Fig 1. Typical Output Characteristics

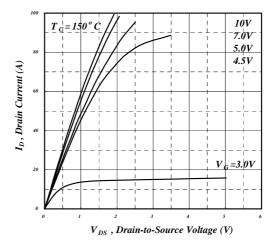


Fig 2. Typical Output Characteristics

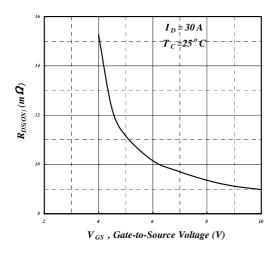


Fig 3. On-Resistance v.s. Gate Voltage

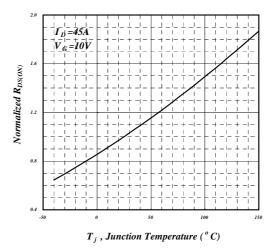


Fig 4. Normalized On-Resistance v.s. Junction Temperature

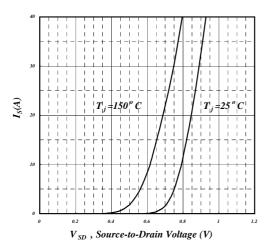


Fig 5. Forward Characteristic of Reverse Diode

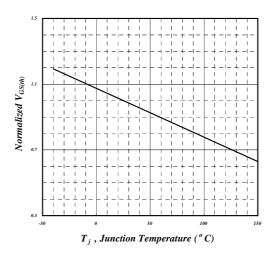


Fig 6. Gate Threshold Voltage v.s.
Junction Temperature

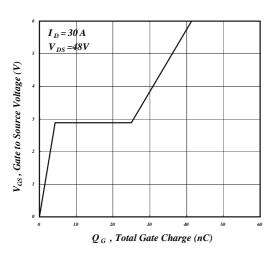


Fig 7. Gate Charge Characteristics

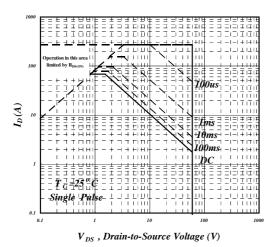


Fig 9. Maximum Safe Operating Area

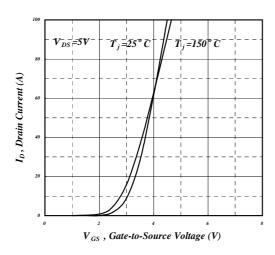


Fig 11. Transfer Characteristics

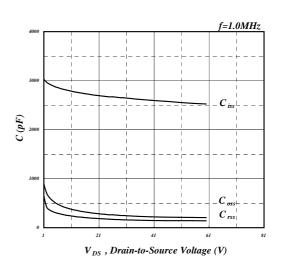


Fig 8. Typical Capacitance Characteristics

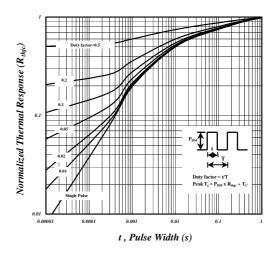


Fig 10. Effective Transient Thermal Impedance

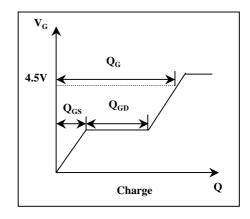
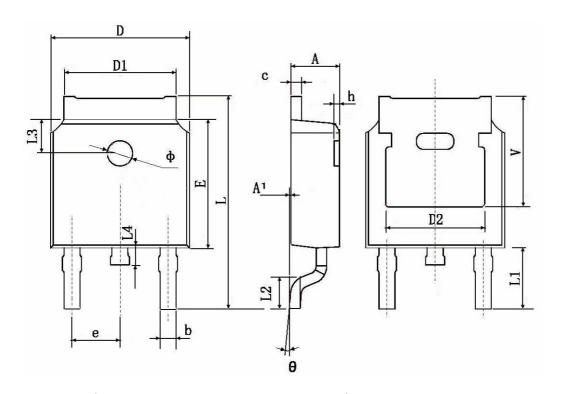


Fig 12. Gate Charge Waveform

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		



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